



**THE DATASHEET OF  
DMN1004UFV-7**



## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C
12V	3.8mΩ @ V <sub>GS</sub> = 4.5V	70A
	5.1mΩ @ V <sub>GS</sub> = 2.5V	55A

## Description

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

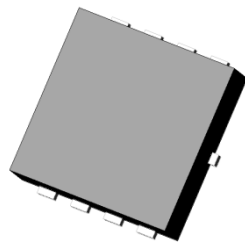
- Power Management Functions
- DC-DC Converters
- Battery

## Features

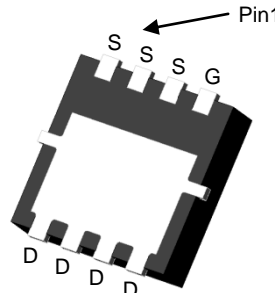
- Low R<sub>DS(ON)</sub> – Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**

## Mechanical Data

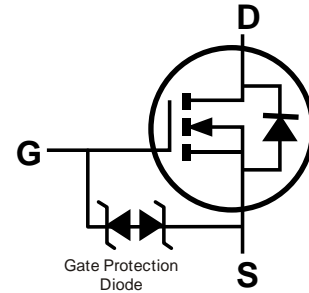
- Case: PowerDI<sup>®</sup> 3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.072 grams (Approximate)



Top View



Bottom View



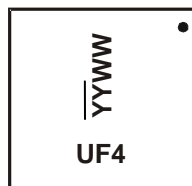
Equivalent Circuit

## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN1004UFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel
DMN1004UFV-13	PowerDI3333-8 (Type UX)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

## Marking Information



UF4 = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Last Two Digits of Year (ex: 16 = 2016)  
 WW = Week Code (01 to 53)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	12	V
Gate-Source Voltage	V <sub>GSS</sub>	±8	V
Continuous Drain Current, V <sub>GS</sub> = 4.5V (Note 7)	I <sub>D</sub>	T <sub>C</sub> = +25°C	70
		T <sub>C</sub> = +70°C	50
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	80	A
Maximum Continuous Body Diode Forward Current (Note 7)	I <sub>S</sub>	70	A
Avalanche Current, L = 0.1mH (Note 8)	I <sub>AS</sub>	34	A
Avalanche Energy, L = 0.1mH (Note 8)	E <sub>AS</sub>	60	mJ

**Thermal Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P <sub>D</sub>	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>θJA</sub>	134	°C/W
Total Power Dissipation (Note 6)	P <sub>D</sub>	1.9	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	66	°C/W
Thermal Resistance, Junction to Case (Note 7)	R <sub>θJC</sub>	3.4	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 9)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	12	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	µA	V <sub>DS</sub> = 9.6V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	µA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 9)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.3	—	1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	2.8	3.8	mΩ	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 15A
		—	3.2	5.1		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 10A
Diode Forward Voltage	V <sub>SD</sub>	—	0.75	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 3.2A
<b>DYNAMIC CHARACTERISTICS</b> (Note 10)						
Input Capacitance	C <sub>iSS</sub>	—	2,385	—	pF	V <sub>DS</sub> = 6V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>oSS</sub>	—	678	—	pF	
Reverse Transfer Capacitance	C <sub>rSS</sub>	—	520	—	pF	
Gate Resistance	R <sub>G</sub>	—	2.2	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>G</sub>	—	26	—	nC	V <sub>DS</sub> = 6V, I <sub>D</sub> = 10A
Total Gate Charge (V <sub>GS</sub> = 8V)	Q <sub>G</sub>	—	47	—	nC	
Gate-Source Charge	Q <sub>GS</sub>	—	2.8	—	nC	
Gate-Drain Charge	Q <sub>GD</sub>	—	5.3	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	5.3	—	ns	V <sub>DD</sub> = 6V, V <sub>GS</sub> = 4.5V, R <sub>G</sub> = 1Ω, I <sub>D</sub> = 5A
Turn-On Rise Time	t <sub>R</sub>	—	10.7	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	31.6	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	16.9	—	ns	
Reverse Recovery Time	t <sub>RR</sub>	—	24.3	—	ns	I <sub>F</sub> = 2A, di/dt = 100A/µs
Reverse Recovery Charge	Q <sub>RR</sub>	—	7.4	—	nC	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - I<sub>AS</sub> and E<sub>AS</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

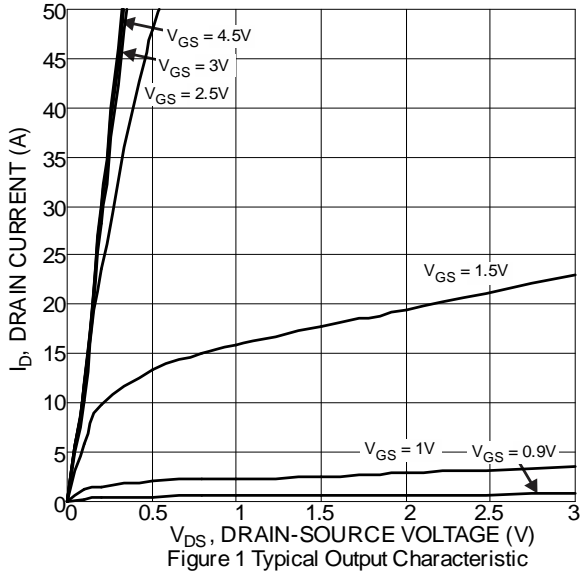


Figure 1 Typical Output Characteristic

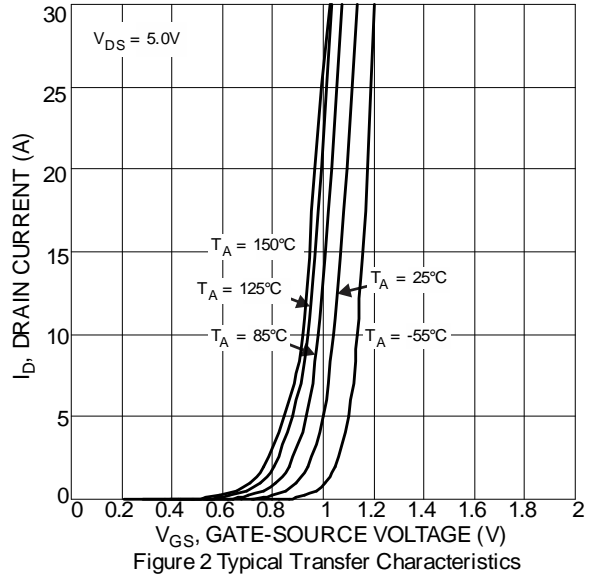


Figure 2 Typical Transfer Characteristics

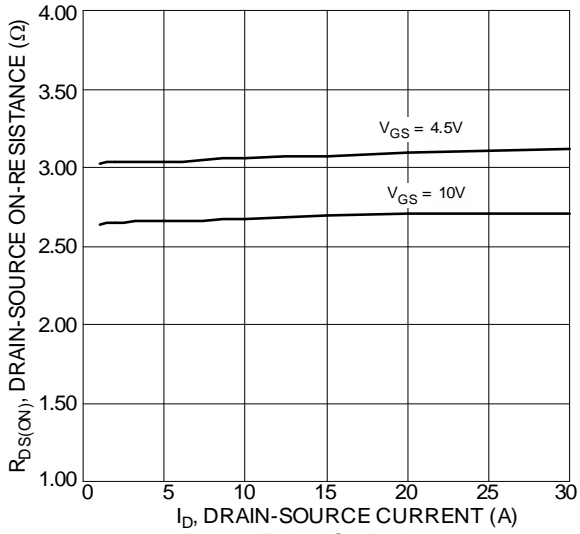


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

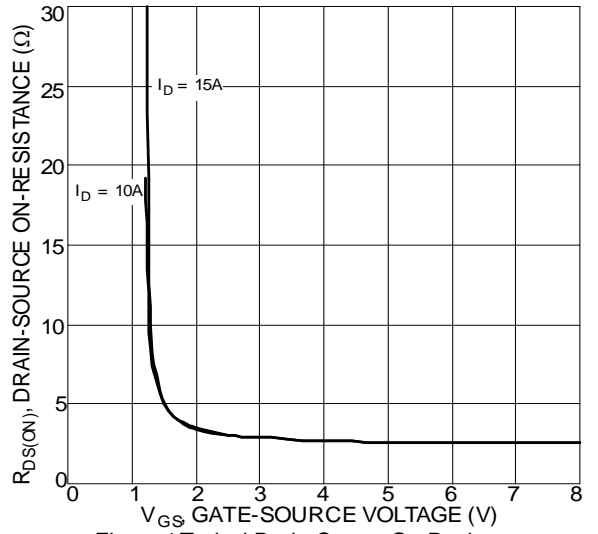


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

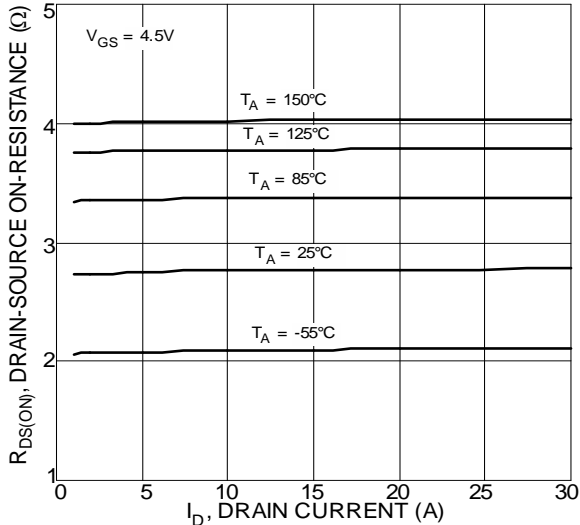


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

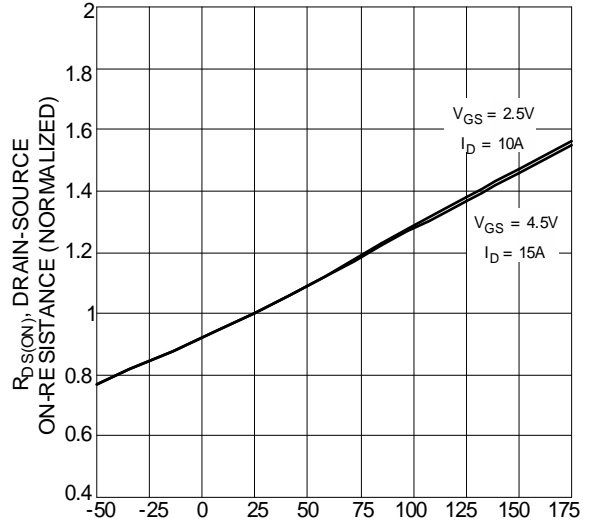


Figure 6 On-Resistance Variation with Temperature

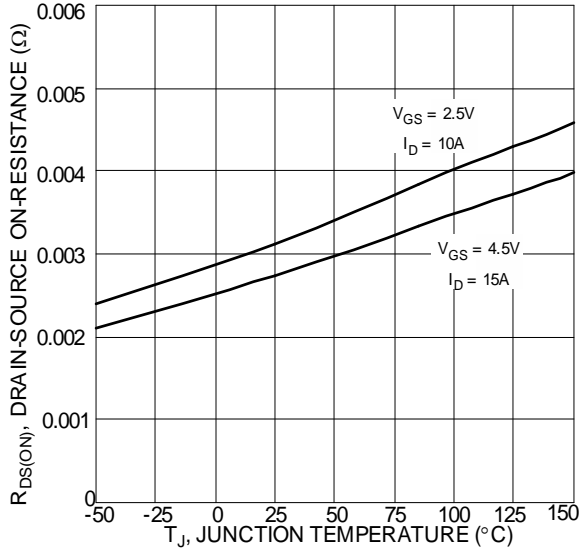


Figure 7 On-Resistance Variation with Temperature

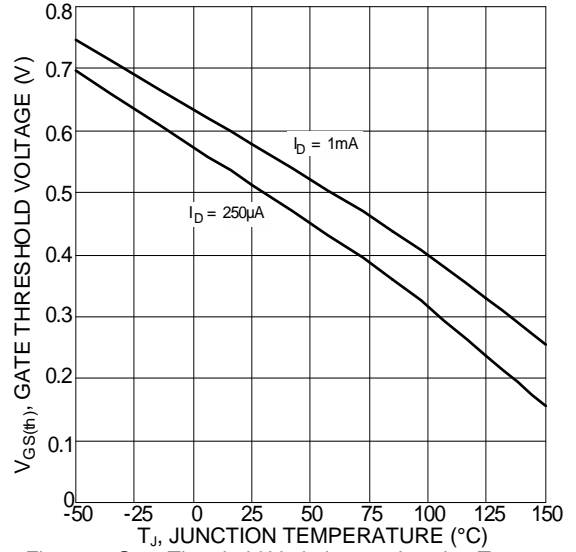


Figure 8. Gate Threshold Variation vs. Junction Temperature

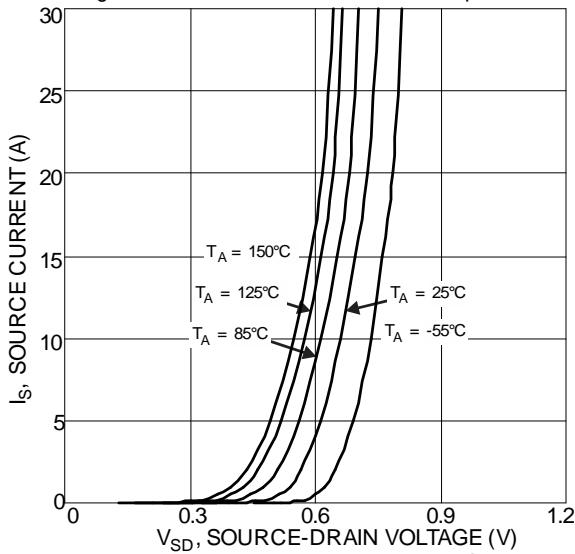


Figure 9 Diode Forward Voltage vs. Current

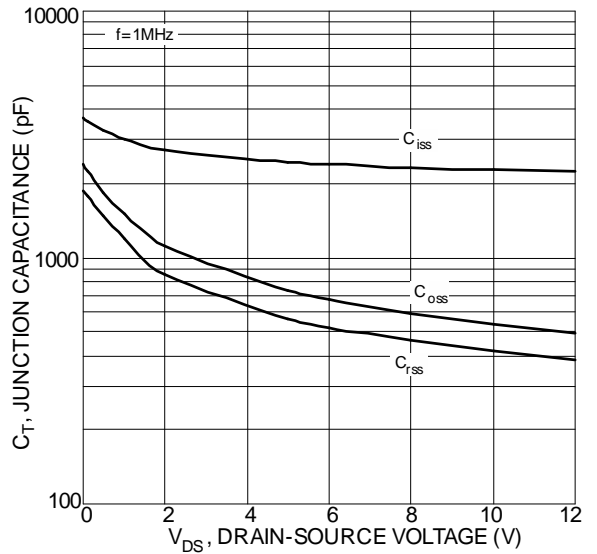


Figure 10 Typical Junction Capacitance

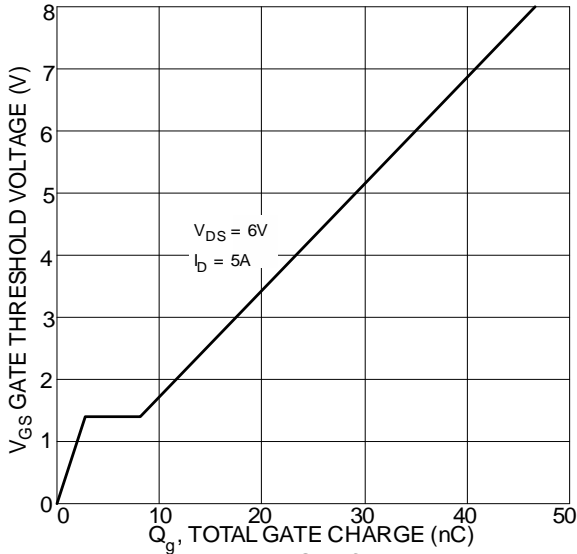


Figure 11 Gate Charge

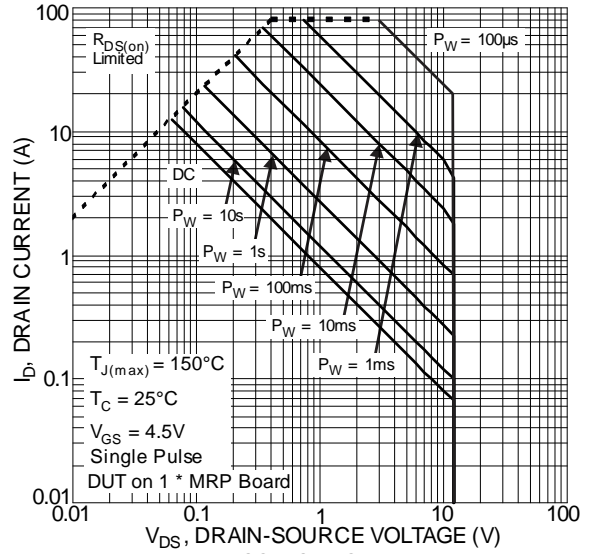
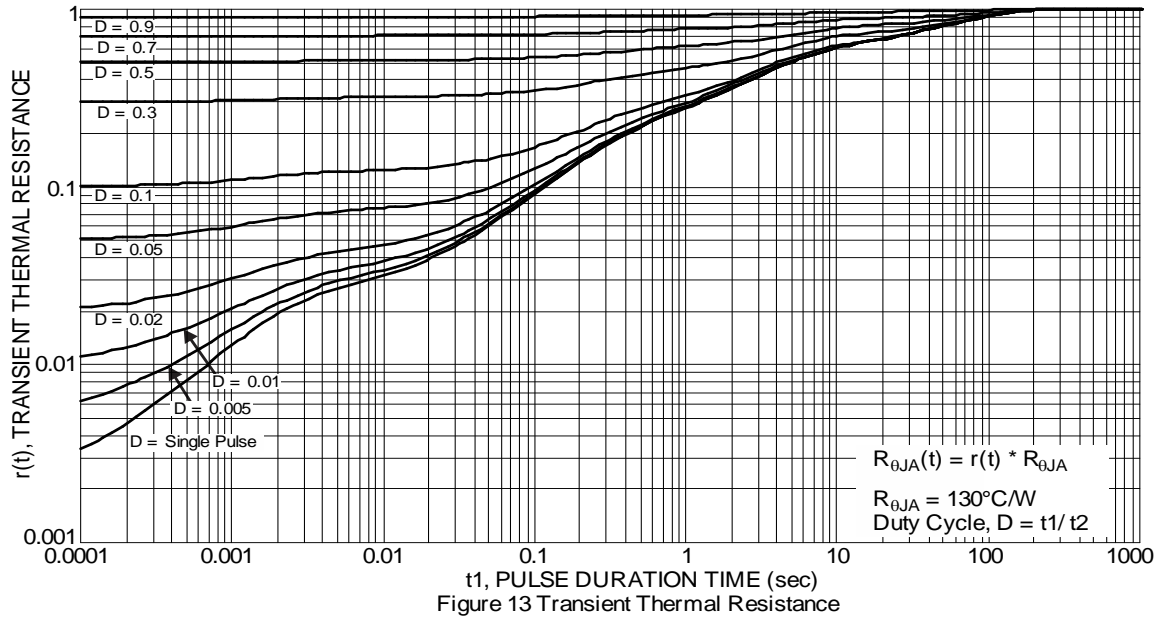


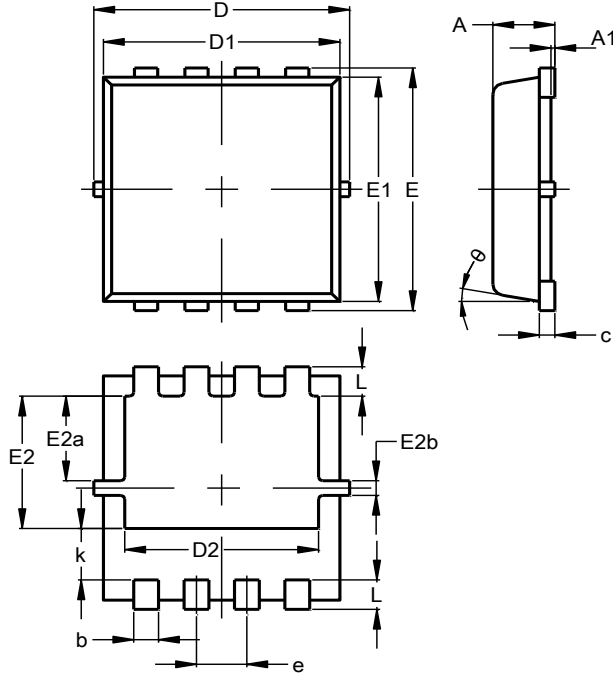
Figure 12 SOA, Safe Operation Area



**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8 (Type UX)**

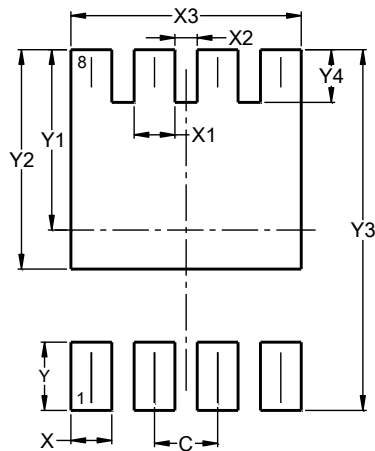


PowerDI3333-8 (Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E2a	0.95	1.35	1.15
E2b	0.10	0.30	0.20
e	0.65 BSC		
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**PowerDI3333-8 (Type UX)**



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540

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